

Low Noise Silicon Bipolar RF Transistor

- Low noise amplifier designed for low voltage applications, ideal for 1.2 V or 1.8 V supply voltage
- Common e.g. in cordless phones, satellite receivers and oscillators up to 22 GHz
- High gain and low noise at high frequencies due to high transit frequency f_T = 45 GHz
- Easy to use Pb-free (RoHS compliant) and halogen free industry standard package with visible leads
- Qualification report according to AEC-Q101 available



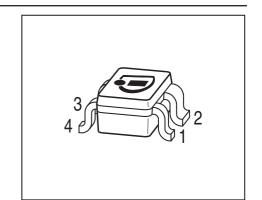


ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package			
BFP520	APs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$		V
T _A = 25 °C		2.5	
<i>T</i> _A = -55 °C		2.4	
Collector-emitter voltage	V _{CES}	10	
Collector-base voltage	V_{CBO}	10	
Emitter-base voltage	V_{EBO}	1	
Collector current	I _C	50	mA
Base current	I _B	5	
Total power dissipation ¹⁾	P _{tot}	125	mW
<i>T</i> _S ≤ 105 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T _{Stg}	-55 150	



 $^{^{1}}T_{\mathrm{S}}$ is measured on the emitter lead at the soldering point to pcb



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	450	K/W

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values		Unit		
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	2.5	3	3.5	V	
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0						
Collector-emitter cutoff current	I _{CES}				nA	
$V_{CE} = 2 \text{ V}, V_{BE} = 0$		-	1	30		
$V_{CE} = 10 \text{ V}, V_{BE} = 0$		-	-	1000		
Collector-base cutoff current	I _{CBO}	-	-	30		
$V_{CB} = 2 \text{ V}, I_{E} = 0$						
Emitter-base cutoff current	I _{EBO}	-	100	3000		
$V_{\rm EB} = 0.5 \rm V, I_{\rm C} = 0$						
DC current gain	h _{FE}	70	110	170	_	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, pulse measured						

 $^{^{1}}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter Parameter $I_A = 25 ^{\circ}\text{C}$, unless	Symbol	Values			Unit		
		min.	typ.	max.			
AC Characteristics (verified by random sampling)							
Transition frequency	f _T	32	45	-	GHz		
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 2 V, f = 2 GHz							
Collector-base capacitance	C _{cb}	-	0.07	0.13	pF		
$V_{\text{CB}} = 2 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,							
emitter grounded							
Collector emitter capacitance	C _{ce}	-	0.3	-			
$V_{CE} = 2 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,							
base grounded							
Emitter-base capacitance	C _{eb}	-	0.33	-			
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,							
collector grounded							
Minimum noise figure	<i>NF</i> _{min}	-	0.95	-	dB		
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,							
<i>f</i> = 1.8 GHz							
Power gain, maximum stable ¹⁾	G _{ms}	-	24	-	dB		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,							
<i>f</i> = 1.8 GHz							
Insertion power gain	$ S_{21} ^2$	-	21.5	-			
V_{CE} = 2 V, I_{C} = 20 mA, f = 1.8 GHz,							
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$							
Third order intercept point at output	IP ₃				dBm		
V_{CE} = 2 V, I_{C} = 20 mA, f = 1.8 GHz,							
$Z_{S} = Z_{Sopt}, Z_{L} = Z_{Lopt}$		-	25	-			
$V_{CE} = 2 \text{ V}, I_{C} = 7 \text{ mA}, f = 1.8 \text{ GHz},$							
$Z_{\rm S} = Z_{\rm Sopt,} Z_{\rm L} = Z_{\rm Lopt}$		-	17	-			
1dB compression point at output	P _{-1dB}						
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,							
$Z_{L} = Z_{Lopt}$, $f = 1.8 \text{ GHz}$		-	12	-			
$I_{\rm C}$ = 7 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,							
$Z_{\rm L} = Z_{\rm Lopt}$, $f = 1.8 \text{GHz}$		-	5	-			

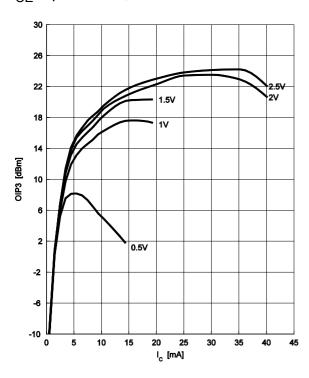
 $^{^{1}}G_{\rm ms} = |S_{21} / S_{12}|$



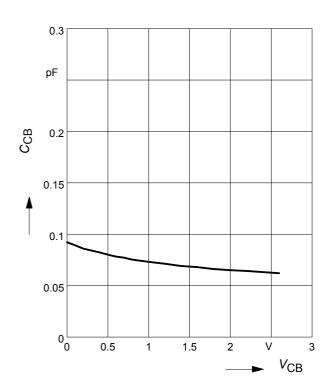
Total power dissipation $P_{tot} = f(T_S)$

140 mW 120 110 100 90 80 70 60 50 40 30 20 10 75 90 105 120 T_{S}

Third order Intercept Point IP_3 = f (I_C) (Output, Z_S = Z_L = 50 Ω) V_{CE} = parameter, f = 900 MHz



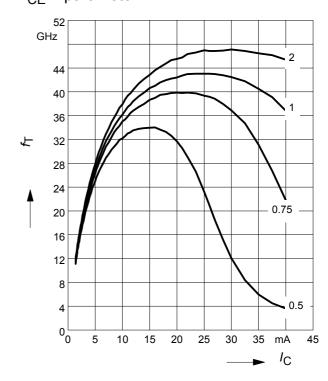
Collector-base capacitance C_{cb} = $f(V_{CB})$ f = 1MHz



Transition frequency $f_T = f(I_C)$

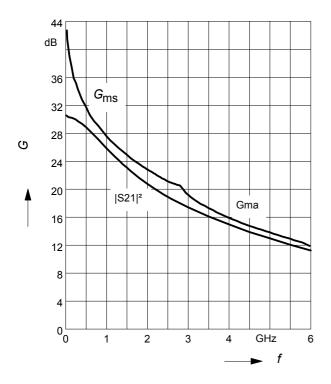
f = 2 GHz

 V_{CE} = parameter in V



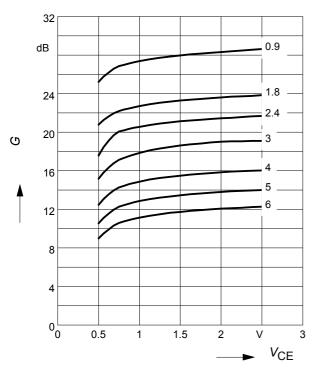


Power gain G_{ma} , G_{ms} , $|S_{21}|^2 = f(f)$ $V_{CF} = 2 \text{ V}$, $I_{C} = 20 \text{ mA}$



Power gain G_{ma} , $G_{\text{ms}} = f(V_{\text{CE}})$ $I_{\text{C}} = 20 \text{ mA}$

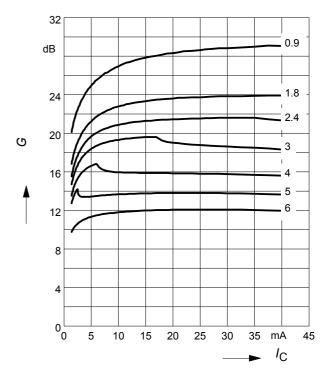
f = parameter in GHz



Power gain G_{ma} , $G_{ms} = f(I_C)$

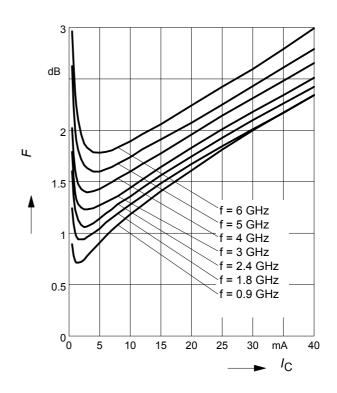
$$V_{CE} = 2V$$

f = parameter in GHz



Minimum noise figure $NF_{min} = f(I_C)$

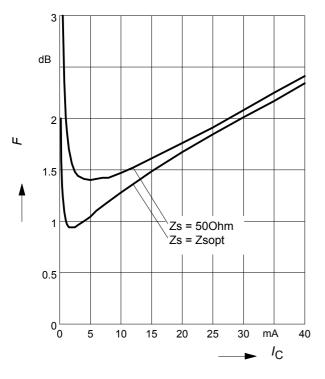
$$V_{CE}$$
 = 2 V, Z_{S} = Z_{Sopt}





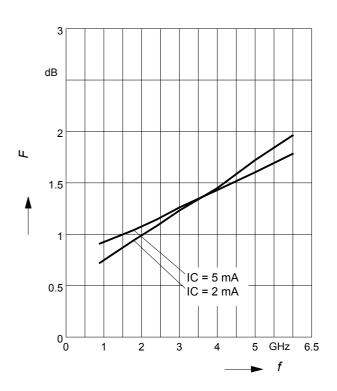
Noise figure $F = f(I_C)$

 $V_{CE} = 2 \text{ V}, f = 1.8 \text{ GHz}$



Minimum noise figure $NF_{min} = f(t)$

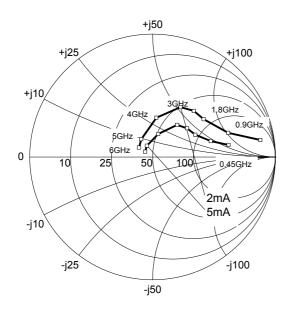
 V_{CE} = 2 V, Z_{S} = Z_{Sopt}



Source impedance for min.

noise figure vs. frequency

 $V_{\rm CE}$ = 2 V, $I_{\rm C}$ = 2 mA / 5 mA





SPICE GP Model

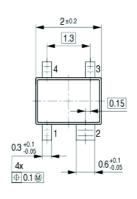
For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

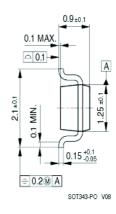
Please consult our website and download the latest versions before actually starting your design. You find the BFP520 SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device. The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP520 SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.



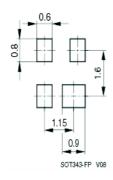
Package Outline



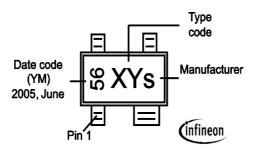




Foot Print

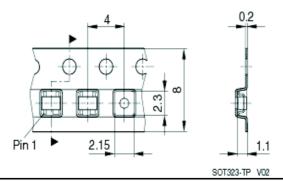


Marking Layout (Example)



Standard Packing

Reel Ø180 mm = 3.000 Pieces/Reel Reel Ø330 mm = 10.000 Pieces/Reel



Package SOT 343.vsd



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Contact Us:

> Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

> Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com